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[Diodes Incorporated](#)
[MMBT3906LP-7](#)

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MMBT3906LP

40V PNP SMALL SIGNAL TRANSISTOR IN DFN1006

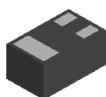
Features

- $BV_{CEO} > -40V$
- $I_C = -200mA$ High Collector Current
- $P_D = 1000mW$ Power Dissipation
- $0.60mm^2$ Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type MMBT3904LP
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

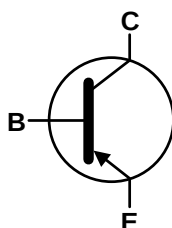
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu,
Solderable per MIL-STD-202, Method 208e4
- Weight: 0.0008 grams (Approximate)

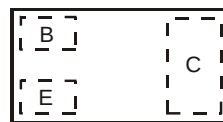
X1-DFN1006-3



Bottom View



Device Symbol



Top View
Device Schematic

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906LP-7	3N	7	8	3,000
MMBT3906LP-7B	3N	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

MMBT3906LP-7	 Top View Dot Denotes Collector Side From date code 1527 (YYWW), this changes to: Top View Bar Denotes Base and Emitter Side
MMBT3906LP-7B	 Top View Bar Denotes Base and Emitter Side 3N = Product Type Marking Code

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current	I _C	-200	mA
Peak Collector Current	I _{CM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

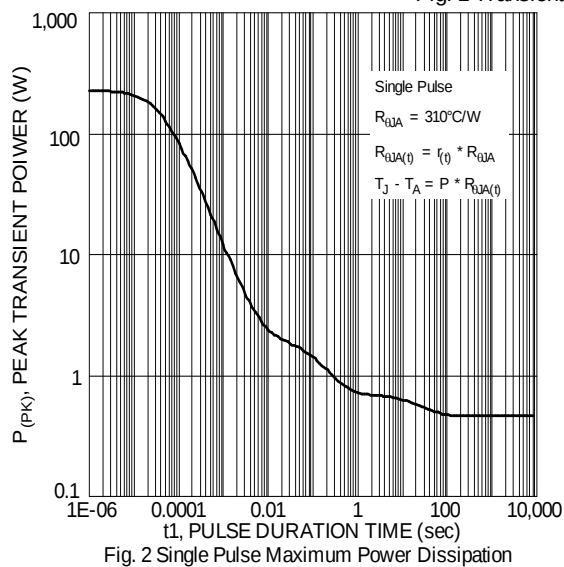
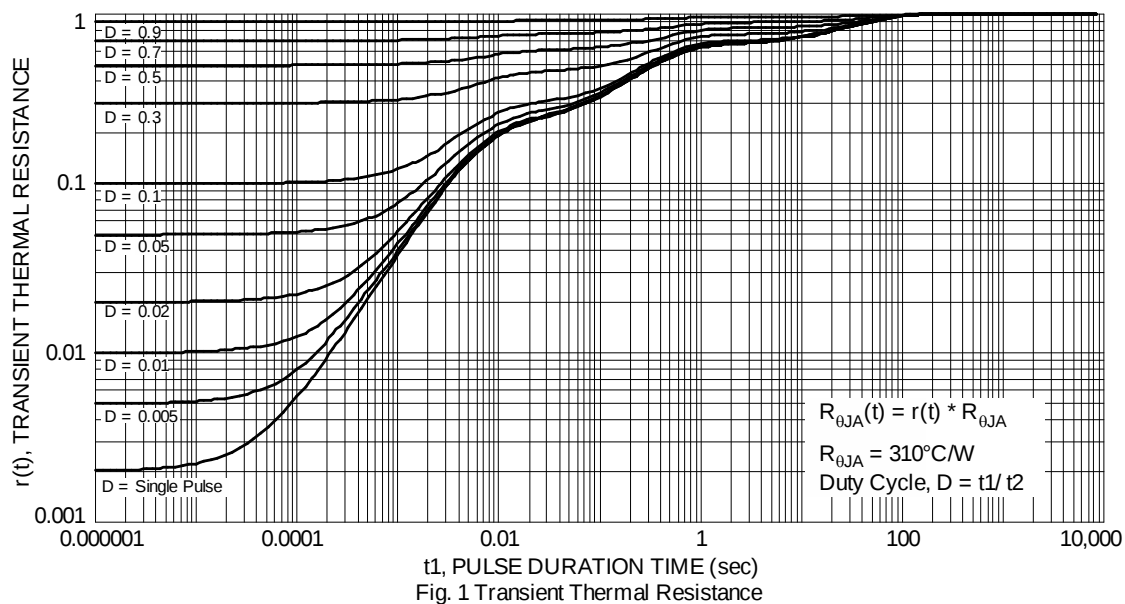
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	400	mW
		1000	
Thermal Resistance, Junction to Ambient	R _{θJA}	310	°C/W
		120	
Thermal Resistance, Junction to Lead	R _{θJL}	120	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	-40	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	—	V	I _C = -10.0mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
	I _{CBO}	—	-50	nA	V _{CB} = -30V, I _E = 0
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h _{FE}	60	—	—	I _C = -100μA, V _{CE} = -1.0V
		80	—		I _C = -1.0mA, V _{CE} = -1.0V
		100	300		I _C = -10mA, V _{CE} = -1.0V
		60	—		I _C = -50mA, V _{CE} = -1.0V
		30	—		I _C = -100mA, V _{CE} = -1.0V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-0.25	V	I _C = -10mA, I _B = -1.0mA
		—	-0.40		I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65	-0.85	V	I _C = -10mA, I _B = -1.0mA
		—	-0.95		I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.5	pF	V _{CB} = -5.0V, f = 1.0MHZ, I _E = 0
Input Capacitance	C _{ibo}	—	10	pF	V _{EB} = -0.5V, f = 1.0MHZ, I _C = 0
Input Impedance	h _{ie}	2.0	12	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	10	× 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHZ
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = -3.0V, I _C = -10mA, V _{BE(off)} = 0.5V, I _{B1} = -1.0mA
Rise Time	t _r	—	35	ns	
Storage Time	t _s	—	225	ns	V _{CC} = -3.0V, I _C = -10mA, I _{B1} = I _{B2} = -1.0mA
Fall Time	t _f	—	75	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

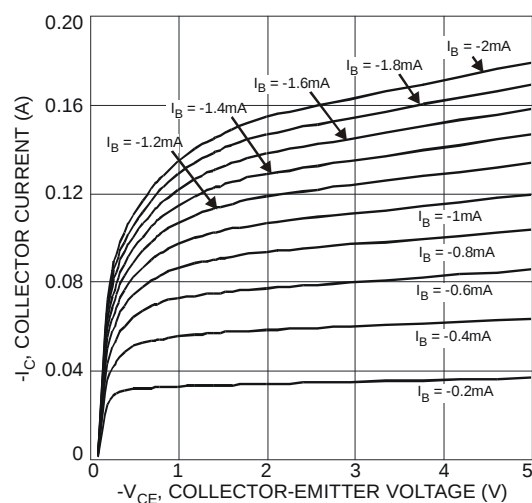


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

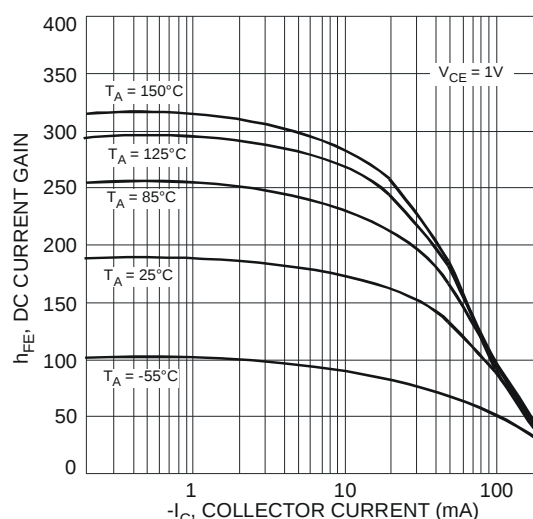


Fig. 5 Typical DC Current Gain vs. Collector Current

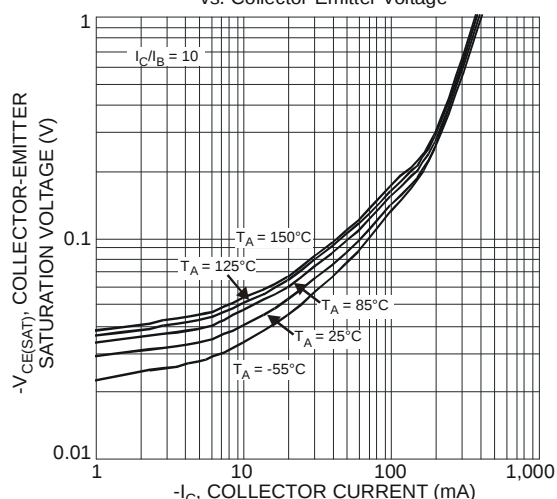


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

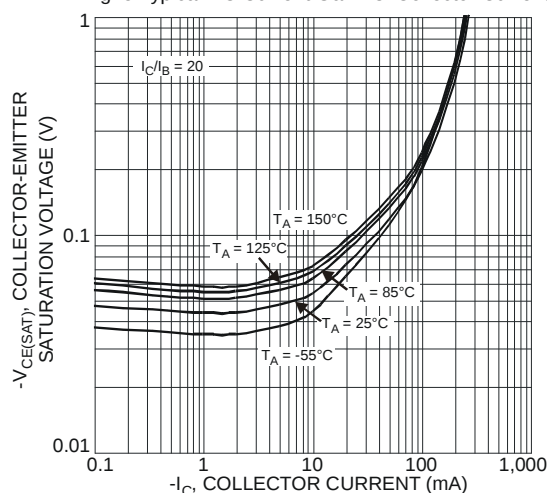


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

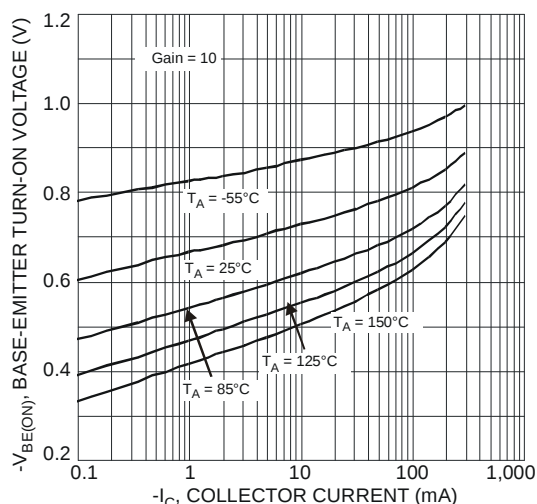


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

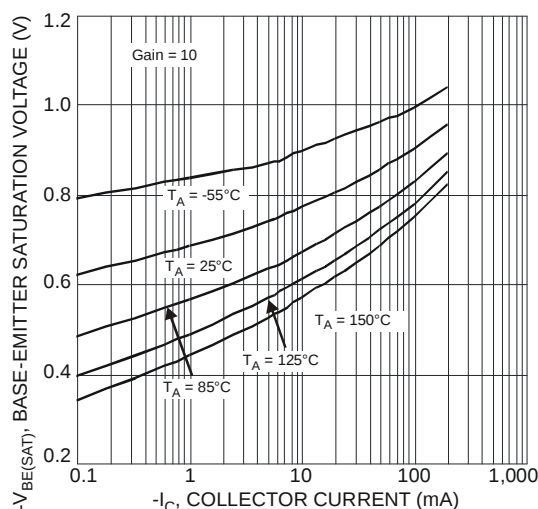
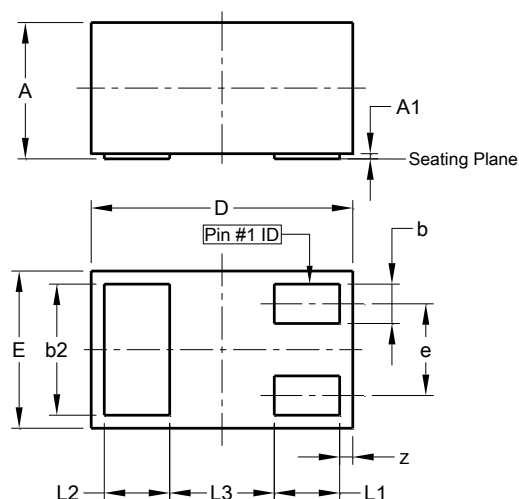


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

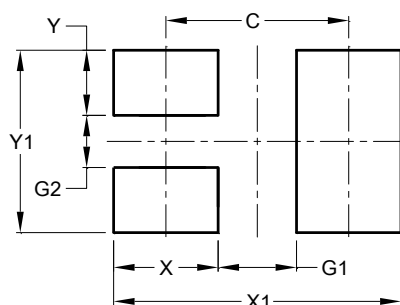


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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